





40V NPN SURFACE MOUNT TRANSISTOR

Features

- Complementary PNP Type Available (MMBT3906LP)
- Ultra-Small Leadless Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

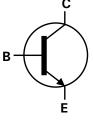
Mechanical Data

- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0008 grams (approximate)

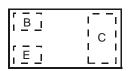
DFN1006-3



Bottom View



Device Symbol



Top View Device Schematic

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3904LP-7	1N	7	8mm	3,000
MMBT3904LP-7B	1N	7	8mm	10,000

Notes

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information

MMBT3904LP-7



Top View Dot Denotes Collector Side

MMBT3904LP-7B



Top View Bar Denotes Base and Emitter Side

1N = Product Type Marking Code



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 4)	I _C	200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_{D}	250	mW
Thermal Resistance, Junction to Ambient (Note 4)	$R_{ heta JA}$	500	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

4. Device mounted on FR-4 PCB pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com

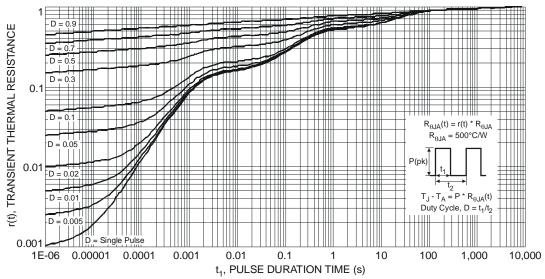
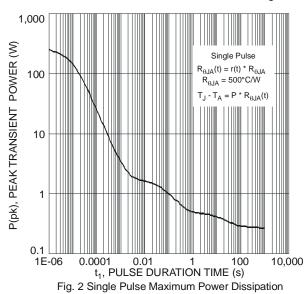


Fig. 1 Transient Thermal Response

0.4

0.3



P_D, POWER DISSIPATION (W) 60 80 100 120 T_A, AMBIENT TEMPERATURE (°C)

Fig. 3 Power Dissipation vs. Ambient Temperature

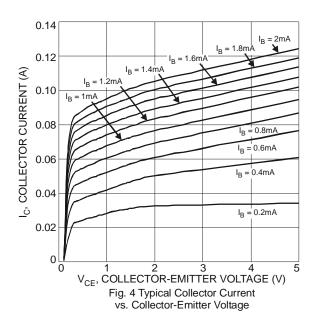
Note 4

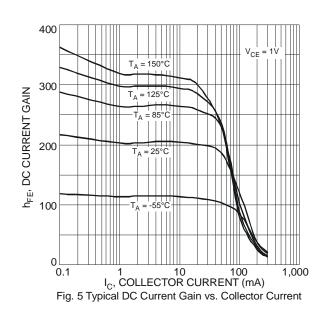


Electrical Characteristics @TA = 25°C unless otherwise specified

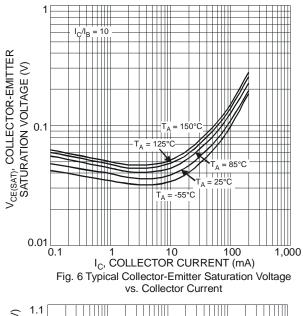
Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	V	$I_C = 10\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 5)	BV _{CEO}	40		V	$I_C = 1.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	_	V	$I_E = 10 \mu A, I_C = 0$	
Collector Cutoff Current	I _{CEX}		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$	
Base Cutoff Current	I_{BL}		50	nA	$V_{CE} = 30V$, $V_{EB(OFF)} = 3.0V$	
ON CHARACTERISTICS (Note 5)						
		40	_		$I_C = 100\mu A, V_{CE} = 1.0V$	
		70	_		$I_C = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$	
DC Current Gain	h _{FE}	100	300	_	$I_C = 10 \text{mA}, V_{CE} = 1.0 \text{V}$	
		60	_		$I_C = 50 \text{mA}, V_{CE} = 1.0 \text{V}$	
		30	_		$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$	
Collector-Emitter Saturation Voltage	Voru		0.20	V	$I_C = 10 \text{mA}, I_B = 1.0 \text{mA}$	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.30		$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
Base-Emitter Saturation Voltage	V _{BE} (sat)	0.65	0.85	V	$I_C = 10 \text{mA}, I_B = 1.0 \text{mA}$	
ŭ		_	0.95		$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$	
Input Capacitance	C _{ibo}	_	8.5	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_{C} = 0$	
Input Impedance	h _{ie}	1.0	10	kΩ		
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$	
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz	
Output Admittance	hoe	1.0	40	μS		
Current Gain-Bandwidth Product	f _T	300	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz	
SWITCHING CHARACTERISTICS						
Delay Time	t _d	_	35	ns	$V_{CC} = 3.0V, I_C = 10mA,$	
Rise Time	t _r		35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$	
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$	
Fall Time	t _f		50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$	

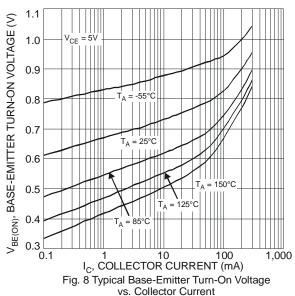
Notes: 5. Short duration pulse test used to minimize self-heating effect.

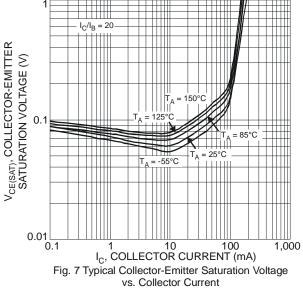


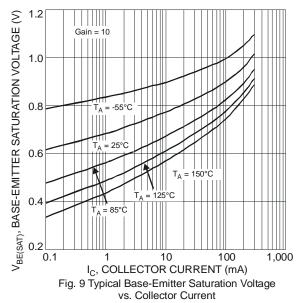




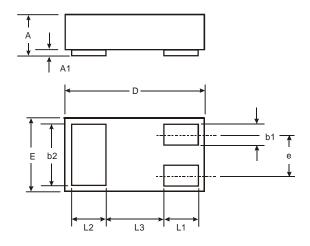








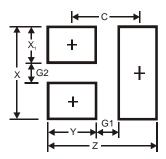
Package Outline Dimensions



DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0	0.05	0.03	
b1	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
е	_		0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	_	_	0.40	
All Dimensions in mm				



Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
С	0.7

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